

SOT-89 Plastic-Encapsulate Transistors

FEATURES

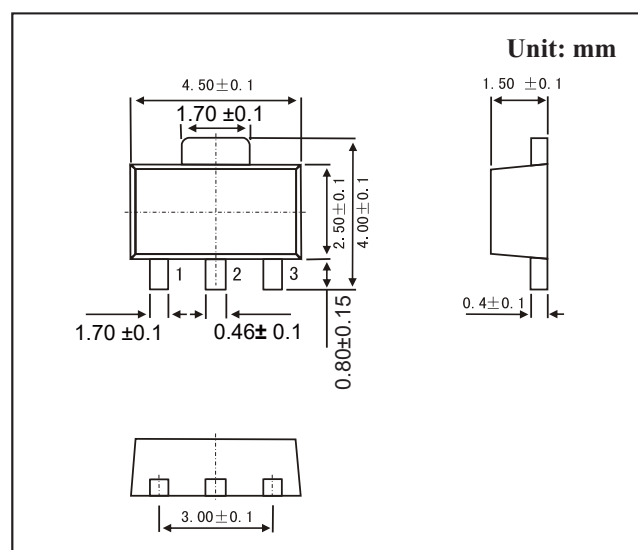
- Suitable For Output Stage of 3 Watts
- Amplifier Small Flat Package
- PC = 1 to 2W (mounted on ceramic substrate)
- Complementary to 2SC2883
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)



Parameter	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-30	V
Collector-Emitter Voltage	VCEO	-30	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-1.5	A
Base Current	IB	-0.3	A
Collector Power Dissipation	PC	500	mW
	PC *	1000	
Jumction temperature	Tj	150	°C
Storage temperature Range	Tstg	- 5 5 t o + 1 5 0	°C

* Mounted on ceramic substrate (250 mm² x 0.8 t)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	VCBO	Ic= -1 mA, IE=0	-30			V
Collector- emitter breakdown voltage	VCEO	Ic= -10 mA, IB=0	-30			
Emitter - base breakdown voltage	VEBO	IE= -1mA, Ic=0	-5			
Collector-base cut-off current	ICBO	VCB= -30 V , IE=0			-100	nA
Emitter cut-off current	IEBO	VEB= -5V , Ic=0			-100	
Collector-emitter saturation voltage	VCE(sat)	Ic=-1.5A, Ib=- 30mA			-2.0	V
Base - emitter saturation voltage	VBE(sat)	Ic=-1.5A, Ib=- 30mA			-1.2	
Base - emitter voltage	VBE	VCE= -2V, Ic=-500 mA			-1	
DC current gain	hFE	VCE= -2V, Ic= -500mA	100		320	
Output capacitance	Cob	VCE= -10V,IE=0,f=1MHz			50	pF
Transition frequency	fr	VCE= -2V, IE= -500mA		120		MHz

RATINGS AND CHARACTERISTIC CURVES

